N-Channel 250-V (D-S) MOSFET

Key Features:

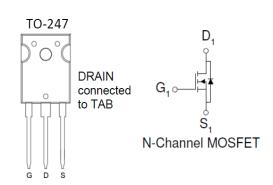
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)		
250	33 @ V _{GS} = 10V	100 ^a		





ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			250	V		
Gate-Source Voltage			±20	V		
Continuous Drain Current a	T _C =25°C	I _D	100 A			
Pulsed Drain Current ^b			400	^		
Continuous Source Current (Diode Conduction) ^a	T _C =25°C	I _S	100	Α		
Power Dissipation ^a	T _C =25°C	P_D	500	W		
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient °	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	0.29	C/VV		

Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

Electrical Characteristics

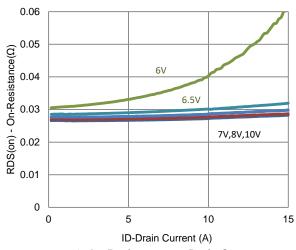
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{GS(th)}$ $V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$				V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 200 V, V _{GS} = 0 V			1	uA	
Zero Gate Voltage Brain Gurrent	DSS	$V_{DS} = 200 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	10		10		
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	75			Α	
Drain-Source On-Resistance a	r _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 15 \text{ A}$			33	mΩ	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 15 \text{ A}$		33		S	
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 30 \text{ A}, V_{GS} = 0 \text{ V}$		0.87		V	
Dynamic ^b							
Total Gate Charge	Q_g	$V_{DS} = 125 \text{ V}, V_{GS} = 10 \text{ V},$		149			
Gate-Source Charge	Q_gs	$V_{DS} = 123 \text{ V}, V_{GS} = 10 \text{ V},$ $I_{D} = 15 \text{ A}$		50		nC	
Gate-Drain Charge	Q_{gd}	1 _D = 10 / 1		46			
Turn-On Delay Time	$t_{d(on)}$	V 425 V D = 9.2 O		75			
Rise Time	t _r	$V_{DS} = 125 \text{ V}, R_L = 8.3 \Omega,$ $I_D = 15 \text{ A},$		75		ne	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		162		ns	
Fall Time	t _f	VGEN = 10 V, NGEN 0 12		60			
Input Capacitance	C_{iss}			8418			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		692		pF	
Reverse Transfer Capacitance	C_{rss}			265			

Notes

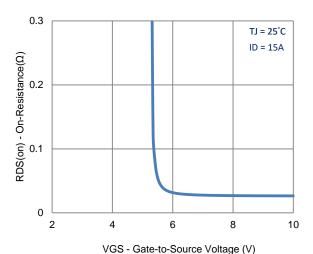
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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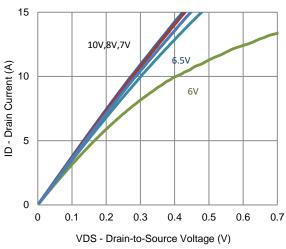
Typical Electrical Characteristics



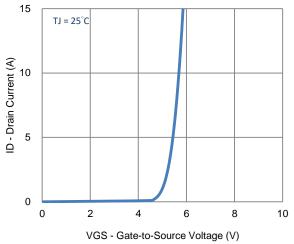
1. On-Resistance vs. Drain Current



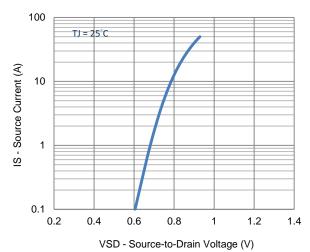
3. On-Resistance vs. Gate-to-Source Voltage



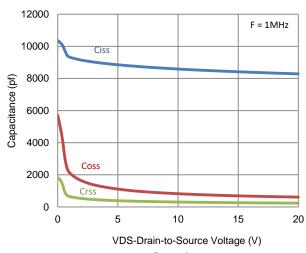
5. Output Characteristics



2. Transfer Characteristics



4. Drain-to-Source Forward Voltage



6. Capacitance

Typical Electrical Characteristics

3

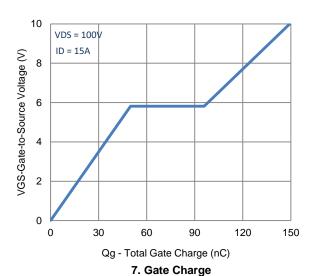
2.5

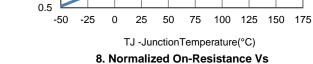
2

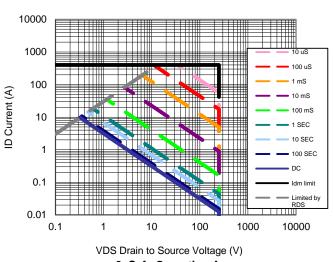
1.5

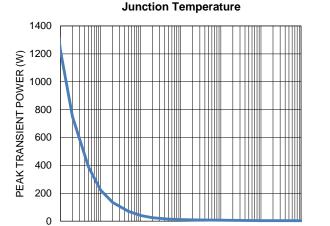
1

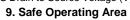
 $RDS(on) \text{ - }On\text{-}Resistance}(\Omega) \\ (Normalized)$











t1 TIME (SEC)

10. Single Pulse Maximum Power Dissipation

1

10

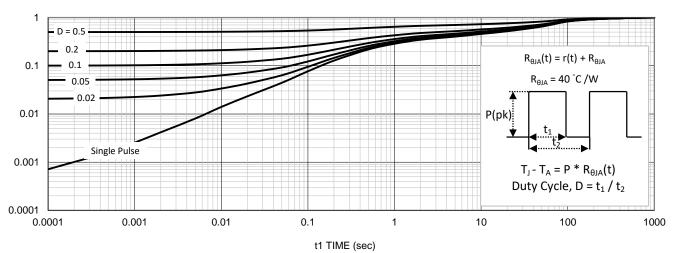
100

1000

0.01

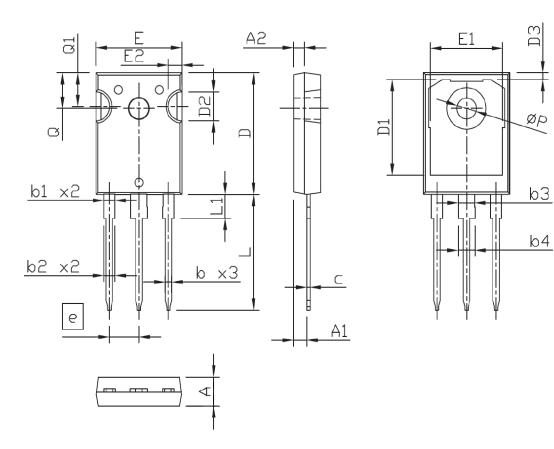
0.1

0.001



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS				
STMBULS	MIN	NDM	MAX		
Α	4,90	5,00	5,10		
A1	2.32	2.42	2.52		
A2	1,90	2,00	2,10		
b	1.17	1.22	1.27		
b1	1.97	2.02	2.07		
b2	2.00	2.10	2.20		
b3	2.97	3.02	3.07		
b4	3.00	3.10 0.62	3.20		
U D	0.59		0.66		
D	20,90	21,00	21,10		
D1	16.25	16.55	16,85		
D2		<u> ۲۲P ا</u>			
D3	1.05 1.20 1.35				
е	5.44 BSC				
Ε	15.70	15.80	15.90		
E1	13.06	13.26	13,46		
E2	2.50 TYP				
L	19.72	19.92	20.12		
L1			4,30		
Q	6.15 BSC				
Q1	5.60	5,80	6.00		
ØΡ	3.55	3.60	3.65		